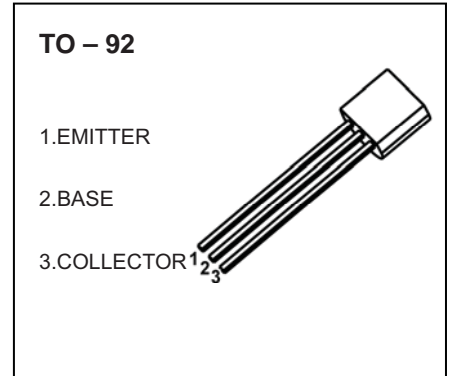


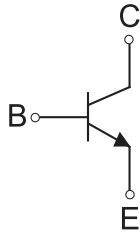
S9018 TRANSISTOR (NPN)

FEATURES

- High Current Gain Bandwidth Product



Equivalent Circuit



ORDERING INFORMATION

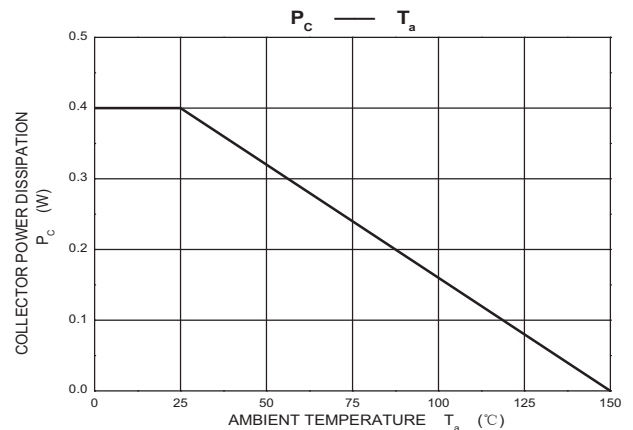
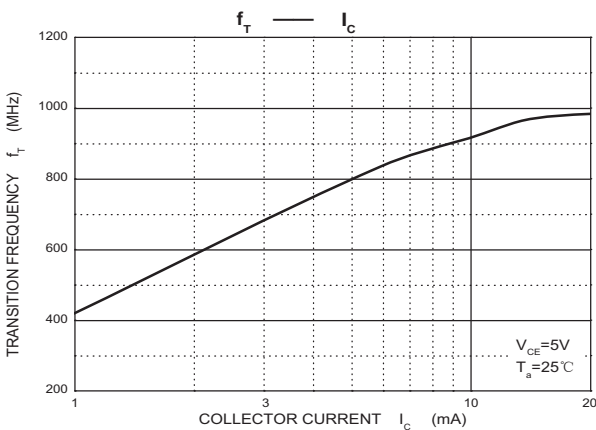
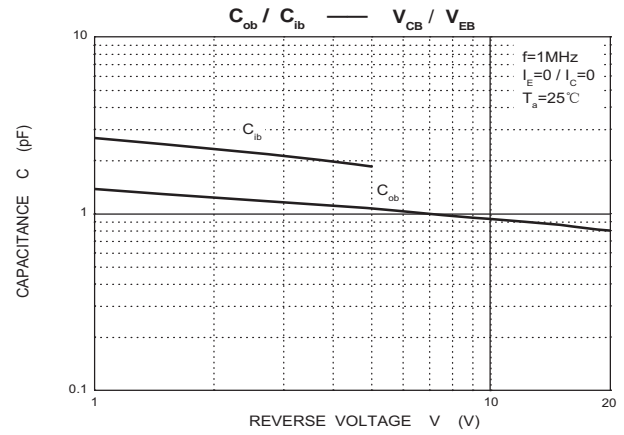
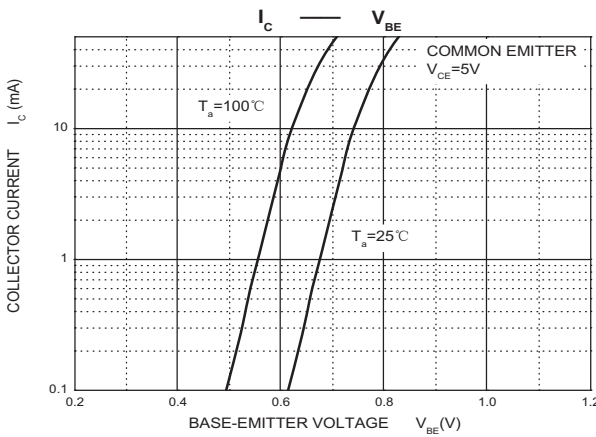
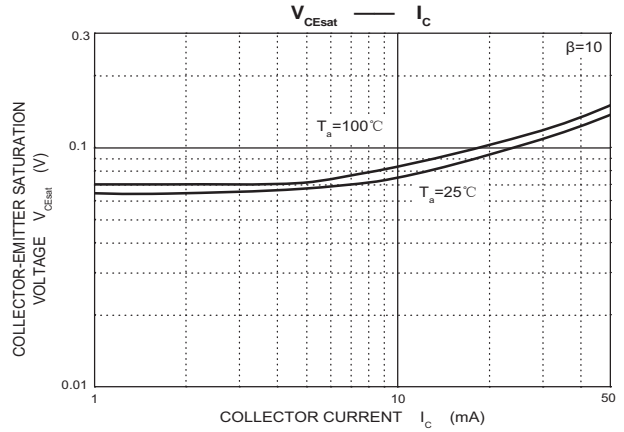
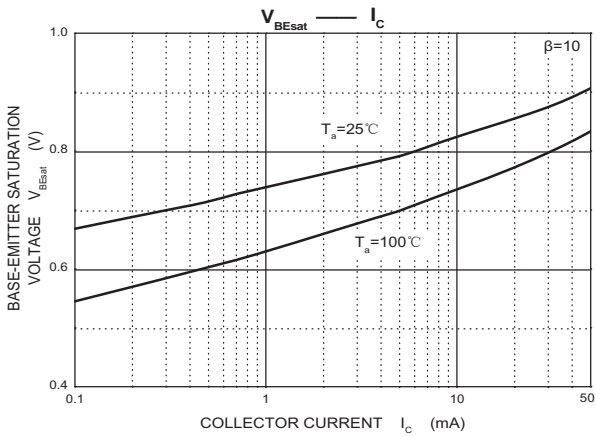
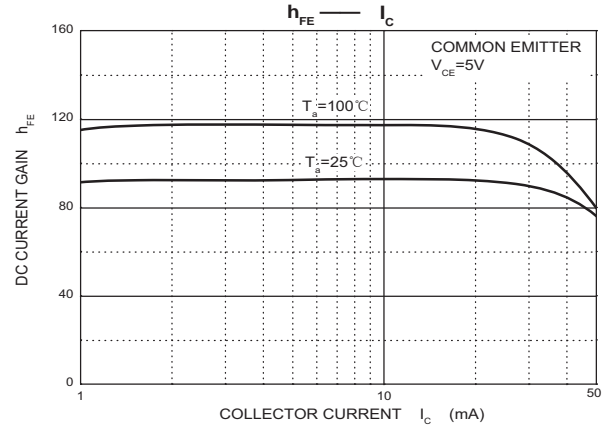
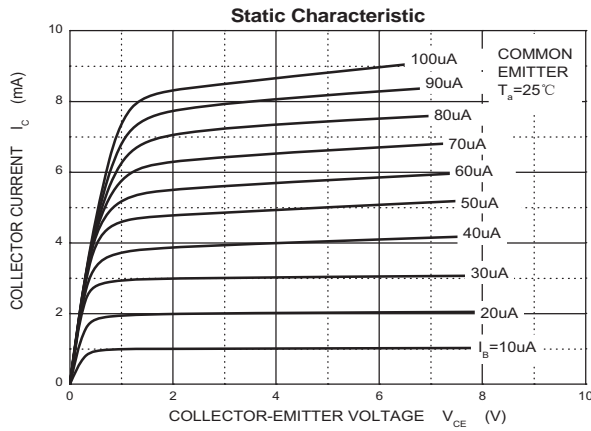
Part Number	Package	Packing Method	Pack Quantity
S9018	TO-92	Bulk	1000pcs/Bag

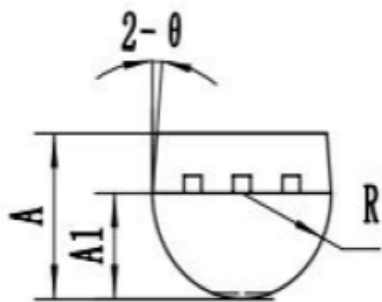
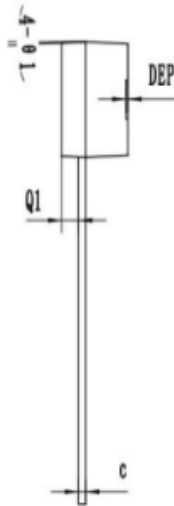
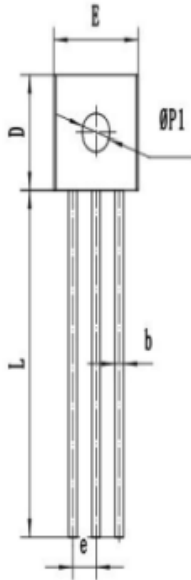
MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CB0}	Collector-Base Voltage	25	V
V _{CEO}	Collector-Emitter Voltage	18	V
V _{EBO}	Emitter-Base Voltage	4	V
I _c	Collector Current -Continuous	0.05	A
P _D	Collector Power Dissipation	400	mW
R _{θJA}	Thermal Resistance from Junction to Ambient	312.5	°C /W
T _J ,T _{stg}	Operation Junction and Storage Temperature Range	-55~+150	°C

$T_a=25^{\circ}\text{C}$ unless otherwise specified

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu\text{A}, I_E=0$	25			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=0.1\text{mA}, I_B=0$	18			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu\text{A}, I_C=0$	4			V
Collector cut-off current	I_{CBO}	$V_{CB}=20\text{V}, I_E=0$			0.1	nA
Collector cut-off current	I_{CEO}	$V_{CE}=15\text{V}, I_B=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=3\text{V}, I_C=0$			0.1	μA
DC current gain	h_{FE}	$V_{CE}=5\text{V}, I_C=1\text{mA}$	28		270	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=10\text{mA}, I_B=1\text{mA}$			0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=10\text{mA}, I_B=1\text{mA}$			1.42	V
Transition frequency	f_T	$V_{CE}=5\text{V}, I_C=50\text{mA}, f=400\text{MHz}$		800		MHz





SYMBOL	MM		
	MIN	NOM	MAX
*A	3.00	3.25	3.50
A1	2.20	2.30	2.40
*b	0.40	0.45	0.50
*c	0.25	0.30	0.35
*D	4.50	4.60	4.70
*E	4.50	4.60	4.70
*e	1.22	1.27	1.32
*L	14.00	14.30	14.60
R	2.20	2.30	2.40
Q1	0.85	0.90	0.95
θ	3°	5°	7°
Ø1	1°	3°	5°
ØP1	1.40	1.50	1.60
DEP	0.05	0.10	0.20

带*为检验尺寸